

### DRIVER FOR SiC-MOSFET MODULES

# VLA586-01R

### **FEATURES**

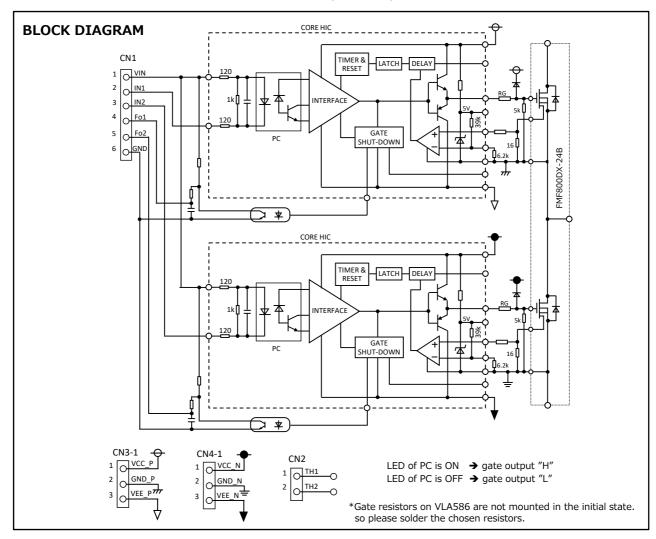
- -Directly mountable on the Full-SiC module
- -Dual gate drive circuits
- -Short circuit detection for sense signal of Full-SiC module
- -Built in short circuit protection with soft gate shut down
- -Output peak gate current is +/-7A(max)
- -Isolation voltage is 2500Vrms (for 1 minute)
- -CMOS compatible input interface

# **TARGETED IGBT MODULES** FMF800DX-24B (MITSUBISHI)

\*Image Photo mounted on Full-SiC module

### **APPLICATIONS**

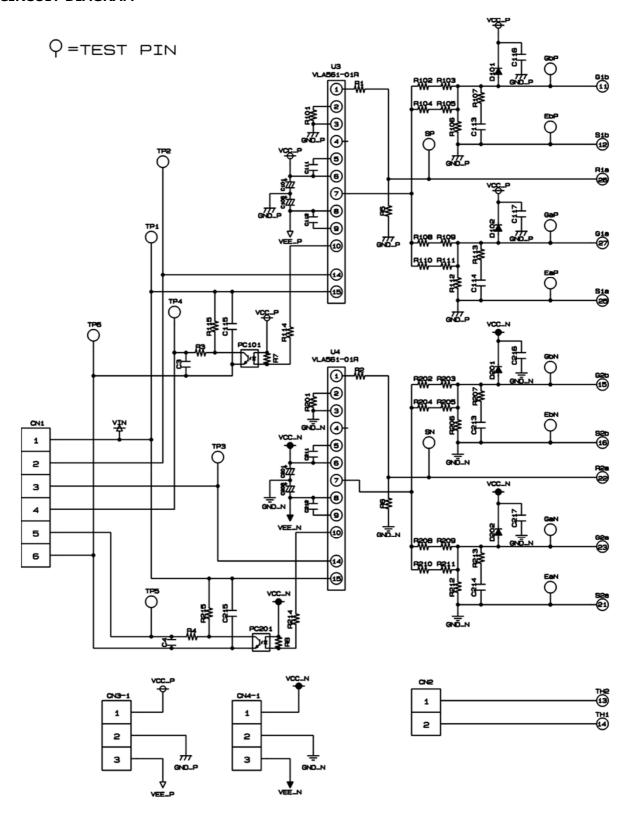
To drive Full-SiC module for inverter, servo amplifier or power unit



DRIVER FOR SiC-MOSFET MODULES

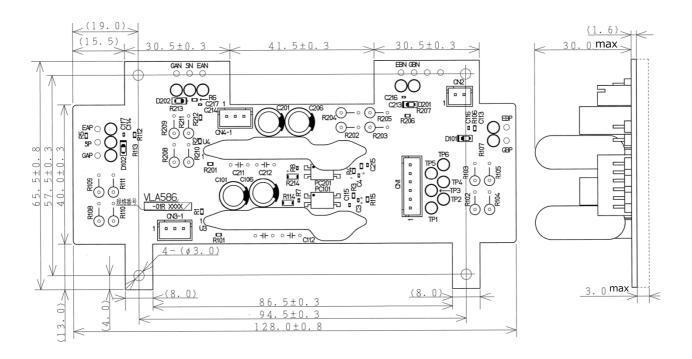


### **CIRCUIT DIAGRAM**

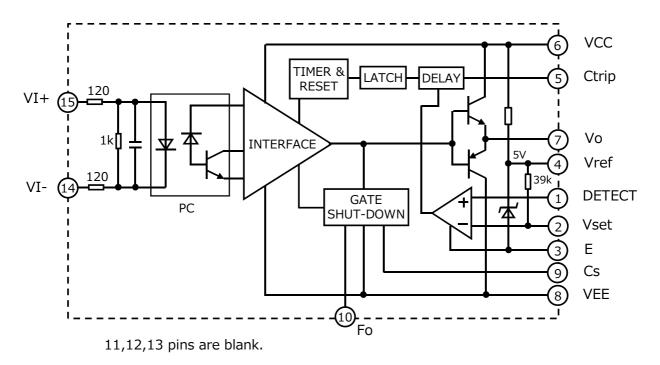


Note.1)Gate resistors are not installed at the time of shipment . Please solder the chosen gate resistors. Note.2) C111 $\sim$ 114,C211 $\sim$ 214, R102 $\sim$ 105,R107 $\sim$ R111,R113,R202 $\sim$ 205,R207 $\sim$ 211,R213 are non-mounted.

**OUTLINE** 単位: mm



### PIN ASSIGNMENT OF INNER CORE HIC





### DRIVER FOR SiC-MOSFET MODULES

## MAXIMUM RATINGS (Unless otherwise noted, Ta=25℃)

Symbol	Item	Conditions	Ratings	Unit	
V <sub>CC</sub>	Supply voltage	DC	18	V	
V <sub>EE</sub>	Supply voltage	ЫС	-15		
VIN	Supply voltage for gate signal	DC	7	٧	
IOHP	Output monte summent	Dulas width 200	-7	А	
IOLP	Output peak current	Pulse width 2us	7	А	
Viso	Isolation voltage between primary and secondary	Sine wave voltage, 60Hz, 1minute	2500	Vrms	
Topr	Operating temperature	No condensation allowable	-25 ~ 70	${\mathbb C}$	
Tstg	Storage temperature	No condensation allowable	-25 ~ 85	${\mathfrak C}$	

### **ELECTRICAL CHARACTERISTICS**

(Unless otherwise noted, Ta=25°C, VCC=16V, VEE=-13V, VIN=5V, RG=2.2 $\Omega$ )

Symbol	Item	Conditions	Limits			Unit
			Min	Тур	Max	Offic
V <sub>CC</sub>	Supply voltage	Recommended range	14	16	17	V
$V_{EE}$			-11	-13	-15	V
VIN	Supply voltage for gate signal	Recommended range	4.75	5	5.25	V
${ m I}_{ m IH}$	"H" input signal current	Recommended range	10	13	16	mA
f	Switching frequency	Recommended range	-	-	20	kHz
RG	Gate resistance	Recommended range	2.2	-	-	Ω
VOH	"H" output voltage	-	14	15	ı	V
VOL	"L" output voltage	-	-11	-12	1	V
tPLH	"L-H" propagation time	$I_{IH}$ =13mA	0.2	0.5	1	us
tr	"L-H" rise time	$I_{IH}$ =13mA	-	0.3	0.8	us
tPHL	"H-L" propagation time	$I_{IH}$ =13mA	0.2	0.4	0.8	us
tf	"H-L" fall time	I <sub>IH</sub> =13mA	-	0.3	0.8	us
ttimer	Timer	Between start and cancel of protection (Under input signal is off state)	1	-	2	ms
Vscth	Threshold voltage of SC detect	Terminal voltage of R1a,R2a on modules	0.63	0.69	0.75	٧
Td_sc	Delay time of SC detect	-	-	1.4	1.8	us
Td_Fo	Delay time of detect signal	-	-	12	20	us





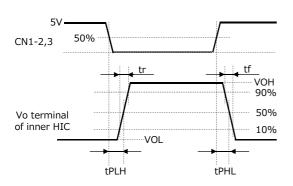
### DRIVER FOR SiC-MOSFET MODULES

Nb

Na

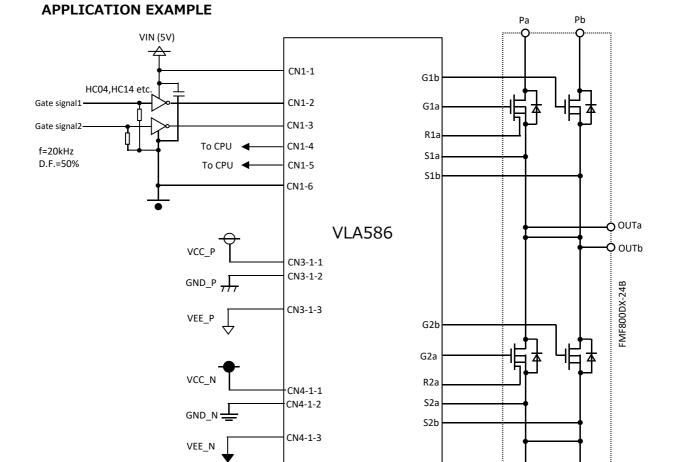
### **DEFFINITION OF CHARACTERISTICS**

### **SWITCHING OPERATION**



\*RG=2.2\Omega, C\_load:0.136uF, f=20kHz, ON Duty=50%

### OPERATION OF SHORT CIRCUIT PROTECTION R1a,R2a Vscth Td\_Fo\_ Vo terminal 0٧ of inner HIC Td\_sc ttimer -5V CN1-4 2.5V---CN1-5 5V 50%



CN1-2,3



### DRIVER FOR SiC-MOSFET MODULES

### **OPERATION OF PROTECTION CIRCUIT**

- (1)FMF800DX-24A shunts the current fixed ratio of drain current to terminal of R1a(R2a). This shunted current flows to detecting resistor(16 $\Omega$ ). This unit detects the short circuit condition by monitoring voltage drop of detecting resistor.
- (2) In case the input signal is "ON" and the terminal voltage of R1a(R2a) is high, this unit will recognize the circuit as short circuit and immediately reduce the gate voltage. Besides, put out Fo signal ("L") which inform that protection circuit is operating at the same time from CN1-4(CN1-5).
- (3) The protection circuit resets and resorts to ordinary condition if input signal is "OFF" when the premised 1~2msec passed. ("OFF" period needs 10us or more)

### LATCH & TIMER RESET SYSTEM IN SHORT-CIRCUIT PROTECTION CIRCUIT

Once the short-circuit protection circuit starts, it shuts down the gate output and keeps Fo output, causing the latch status. This status is canceled if the input signal is OFF when specific time passed after the activation of the short-circuit protection circuit. Then, gate output depending on input signals becomes possible. If the input signal is ON when specific time elapses, the latch status is not canceled: it is canceled when the signal becomes OFF.

As mentioned above, on the latch & timer reset system, the latch status is resulted after activation of the protection circuit and shutdown of the gate output. Therefore, during this period, gate output is not made no matter how much input signals are received. For this reason, it is possible to safely stop the entire equipment by sending error signals to the microcomputer during this period to stop all gate signals.

# DETECTION OF SHORT CIRCUIT GATE SHUTDOWN TIMER START OUTPUT FAULT SIGNAL END OF TIMER TIMER 1 ~ 2ms CLEAR FAULT SIGNAL ENABLE OUTPUT

**OPERATION FLOW ON DETECTING SHORT CIRCUIT** 



DRIVER FOR SiC-MOSFET MODULES

### FOR SAFETY USING

Great detail and careful attention are given to the production activity of Devices, such as the development, the quality of production, and in it's reliability. However the reliability of Devices depends not only on their own factors but also in their condition of usage. When handling Devices, please note the following cautions.

CALITIONIC					
	CAUTIONS				
Packing	The materials used in packing Devices can only withstand normal external conditions. When exposed to outside shocks, rain and certain environmental contaminators, the packing materials will deteriorates. Please take care in handling.				
Carrying	<ol> <li>Don't stack boxes too high. Avoid placing heavy materials on boxes.</li> <li>Boxes must be positioned correctly during transportation to avoid breakage.</li> <li>Don't throw or drop boxes.</li> <li>Keep boxes dry. Avoid rain or snow.</li> <li>Minimal vibration and shock during transportation is desirable.</li> </ol>				
Storage	<ul> <li>When storing Devices, please observe the following notices or possible deterioration of their electrical characteristics, risk of solder ability, and external damage may occur.</li> <li>1) Devices must be stored where fluctuation of temperature and humidity is minimal, and must not be exposed to direct sunlight. Store at the normal temperature of 5 to 30 degrees Celsius with humidity at 40 to 60%.</li> <li>2) Avoid locations where corrosive gasses are generated or where much dust accumulates.</li> <li>3) Storage cases must be static proof.</li> <li>4) Avoid putting weight on boxes.</li> </ul>				
Extended storage	When extended storage is necessary, Devices must be kept non-processed. When using Devices which have been stored for more than one year or under severe conditions, be sure to check that the exterior is free from flaw and other damages.				
Maximum ratings	To prevent any electrical damages, use Devices within the maximum ratings. The temperature, current, voltage, etc. must not exceed these conditions.				
Polarity	To protect Devices from destruction and deterioration due to wrong insertion, make sure of polarity in inserting leads into the board holes, conforming to the external view for the terminal arrangement.				





DRIVER FOR SiC-MOSFET MODULES

### Keep safety first in your circuit designs!

·ISAHAYA Electronics Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (1) placement of substitutive, auxiliary circuits, (2) use of non-flammable material or (3) prevention against any malfunction or mishap.

### Notes regarding these materials

- •These materials are intended as a reference to our customers in the selection of the ISAHAYA products best suited to the customer's application; they don't convey any license under any intellectual property rights, or any other rights, belonging to ISAHAYA or a third party.
- ·ISAHAYA Electronics Corporation assumes no responsibility for any damage, or infringement of any third party's rights, originating in the use of any product data, diagrams, charts or circuit application examples contained in these materials.
- ·All information contained in these materials, including product data, diagrams and charts, represent information on products at the time of publication of these materials, and are subject to change by ISAHAYA Electronics Corporation without notice due to product improvements or other reasons. It is therefore recommended that customers contact ISAHAYA Electronics Corporation or an authorized ISAHAYA products distributor for the latest product information before purchasing product listed herein. ·ISAHAYA Electronics Corporation products are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Please contact ISAHAYA Electronics Corporation or an authorized ISAHAYA products distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.
- $\cdot$ The prior written approval of ISAHAYA Electronics Corporation is necessary to reprint or reproduce in whole or in part these materials.
- If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination.

Any diversion or re-export contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited.

•Please contact ISAHAYA Electronics Corporation or authorized ISAHAYA products distributor for further details on these materials or the products contained therein.